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| CERTII Applicant(| | NSMISSION BY FAC | SIMILE (37 CFR 1.8) | Docket No. SC11464ZP | |
| 1 | ial No. 29,093 | Filing Date 12/21/2001 | Examiner Unknown | Group Art Unit 2811 | |
| Invention: | TRY FOR ETCHING | G QUATERNARY INTER | FACE LAYERS ON InGaAsP MC | OSTLY FORMED BETWEEN | |
| I hereby certify that thisis being facsimile transmitted to the | | the United States Patent | Power of Attorney (Identify type of correspondence) e United States Patent and Trademark Office (Fax. No. 703-308-7382 | | |
| on | June 9, 2003 | | | | |
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

POWER OF ATTORNEY

Docket No.

SC11464ZP

Name of Applicant:

Mariam G. Sadaka et al.

Address of Applicant: 3119 Napa Drive

Austin, TX 78738

Title:

A CHEMISTRY FOR ETCHING QUATERNARY INTERFACE LAYERS ON

InGaAsP MOSTLY FORMED BETWEEN GAAS AND InxGa(1-x)P LAYERS

Serial No., if Any:

10/029,093

Filed:

12/21/2001

TO THE COMMISSIONER FOR PATENTS

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Honorable Sir.

I hereby appoint:

John A. Fortkort Reg. No. 38,454

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as principal atternays to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to:

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POSE/DEVA1